

surface of the substrate; a high dope n-type amorphous silicon layer 16 is formed with an intrinsic amorphous silicon layer 15 interposed on a rear surface side of the substrate 10. A transparent electrode 17 on a rear surface side formed of ITO is formed on an entire surface of the high dope n-type amorphous silicon layer 16, and a comb-shaped collector 18 of silver (Ag) or the like is formed thereon. The rear surface also has a BSF structure which the intrinsic amorphous silicon layer is sandwiched between the crystalline silicon substrate and a high dope amorphous silicon layer in order to reduce defects on the interface and improve characteristics of the hetero junction interface.

Please replace the Page 11, lines 16-22 with the following paragraph:

Heat resistance films of PVF (polyvinyl fluoride), PVDF (polyvinylidene Fluoride), FEP (fluoropropylene-copolymer), ETFE (2-ethylene-4-fluoroethylene-copolymer) PC (polycarbonate), PVC (polyvinyl chloride), PMMA (polymethylmethacrylate), other than PET (polyethylene terephthalate) can be used as the rear surface resin film 5. The water transmission preventing layer 7a is formed by depositing inorganic oxide (aluminum oxide, silicon oxide), nitride (SiN), fluoride (HgF, CaF) or the like on the heat resistance film. Because of water barrier property provided with the inorganic oxide, the layer 7a can function for preventing water transmission.

IN THE CLAIMS:

Please amend claim 7 as follows:

7. Amended) The solar cell module according to claim 1, wherein the water transmission preventing layer is formed so as to cover the interval part between the solar cell elements.